

TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process) (Bias Resistor built-in Transistor)

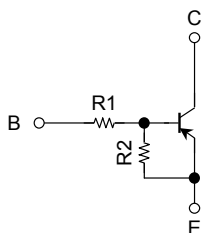
## RN2101FS,RN2102FS,RN2103FS RN2104FS,RN2105FS,RN2106FS

Switching, Inverter Circuit, Interface Circuit and  
Driver Circuit Applications

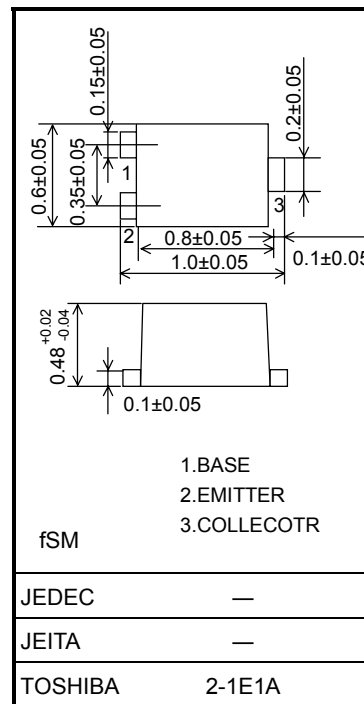
Unit: mm

- Incorporating a bias resistor into a transistor reduces parts count.  
Reducing the parts count enable the manufacture of ever more compact equipment and save assembly cost.
- Complementary to RN1101FS~RN1106FS

### Equivalent Circuit and Bias Resistor Values



Type No.	R1 (kΩ)	R2 (kΩ)
RN2101FS	4.7	4.7
RN2102FS	10	10
RN2103FS	22	22
RN2104FS	47	47
RN2105FS	2.2	47
RN2106FS	4.7	47



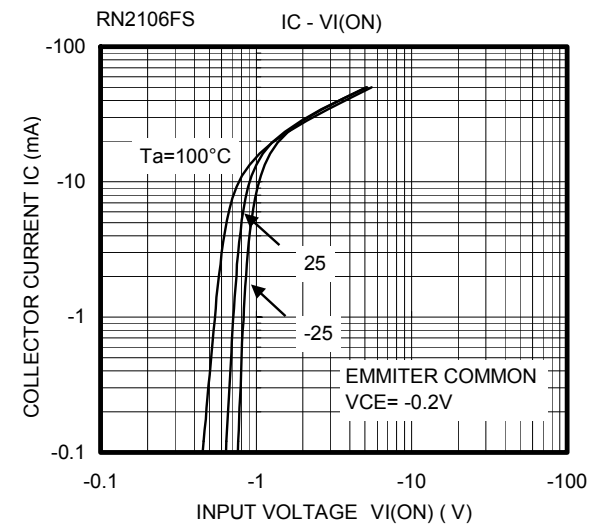
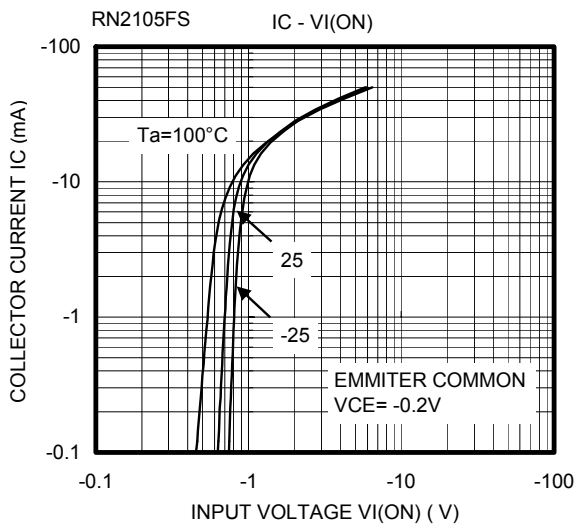
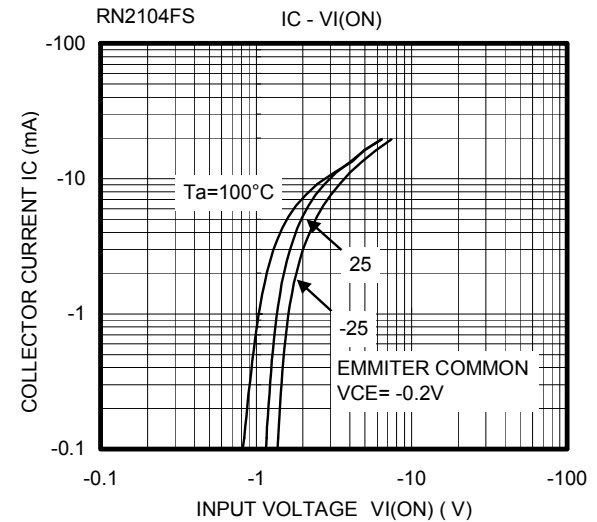
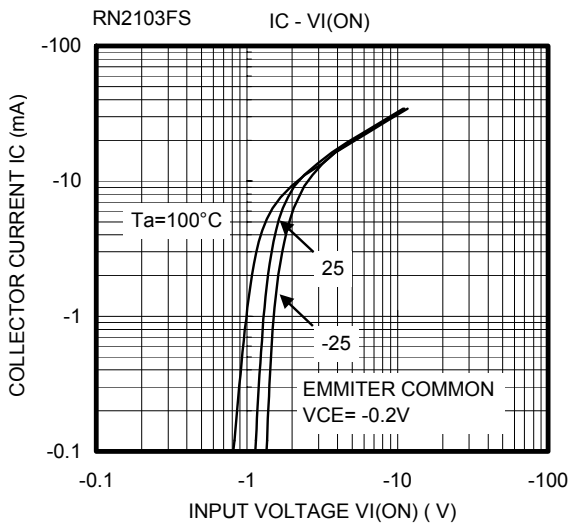
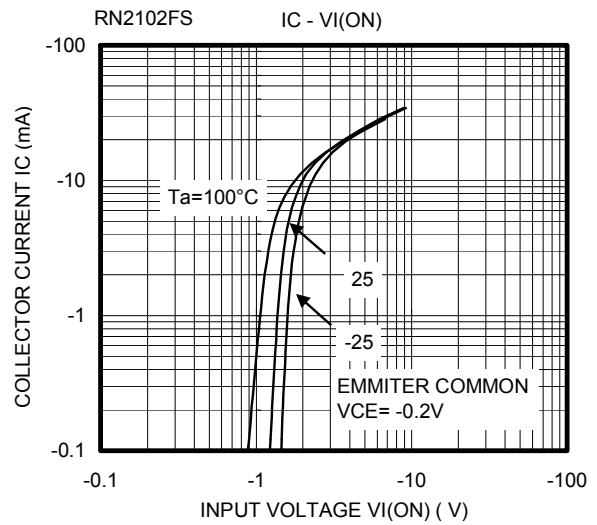
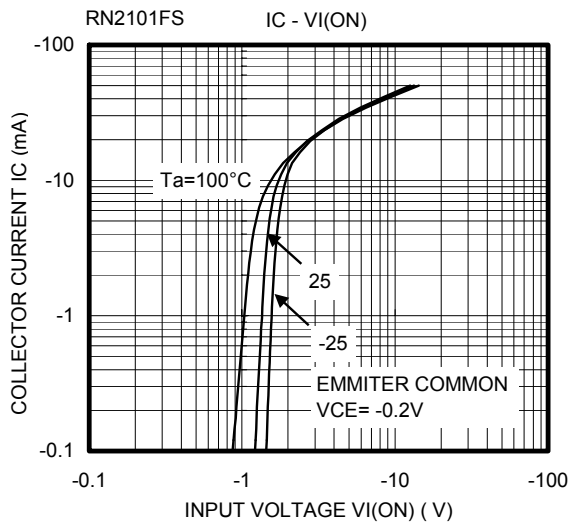
Weight:0.0006g (typ.)

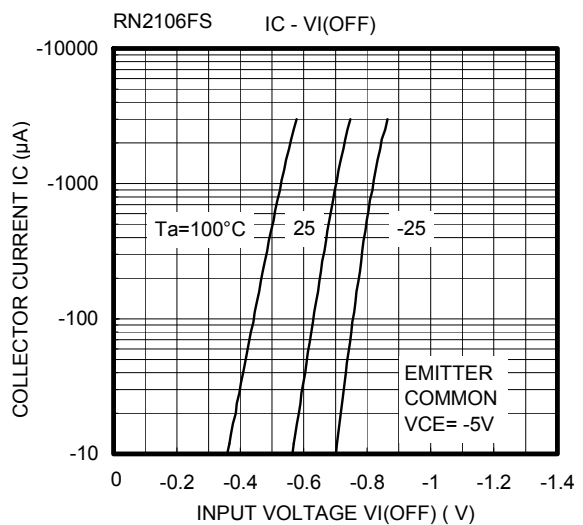
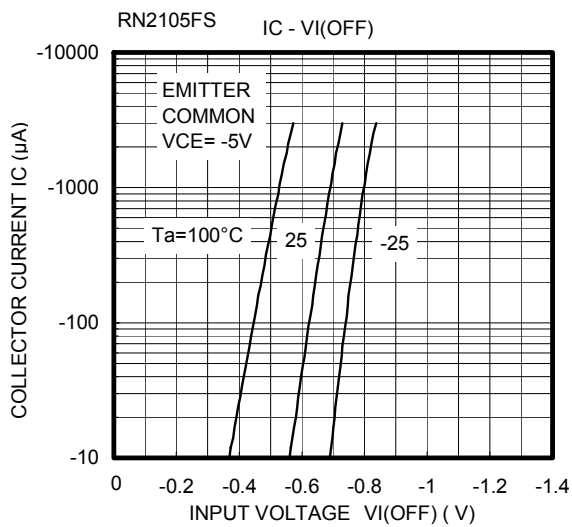
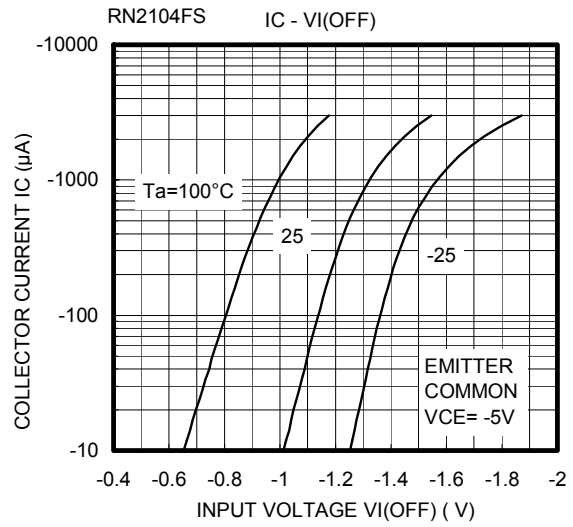
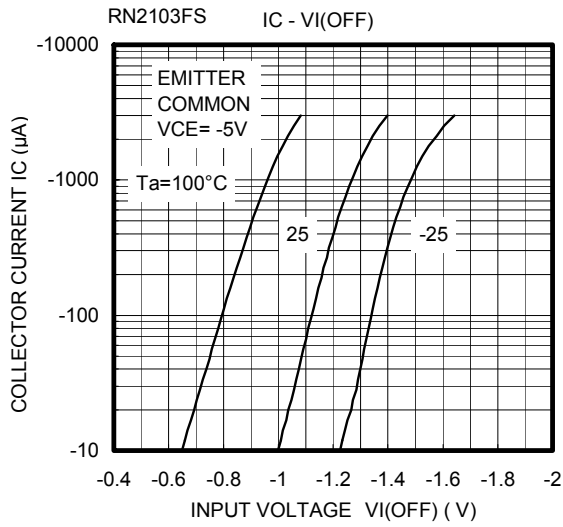
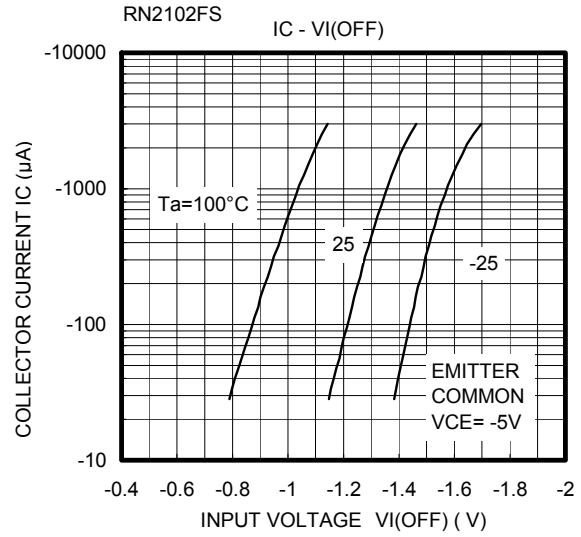
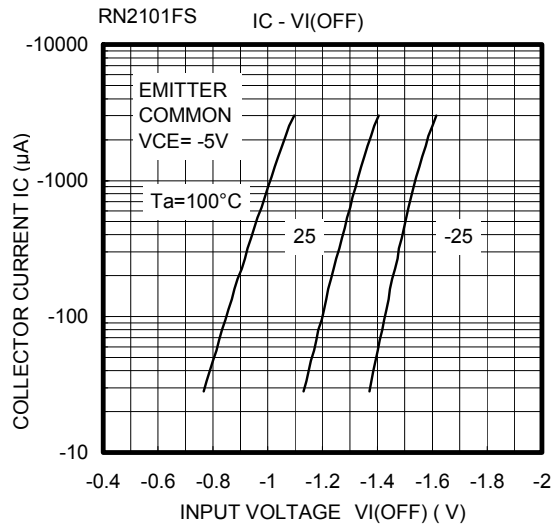
### Maximum Ratings (Ta = 25°C)

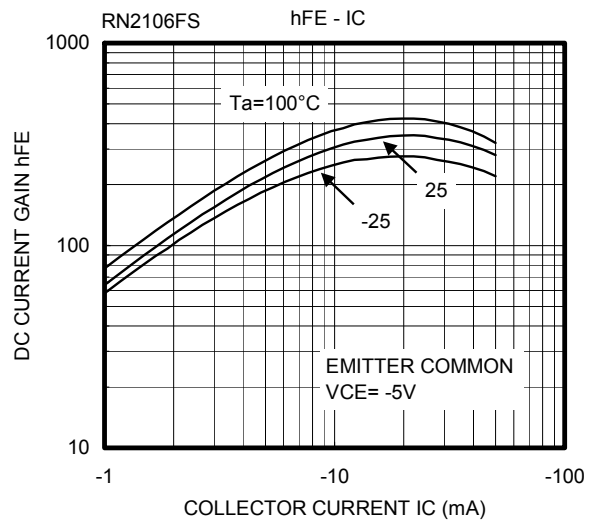
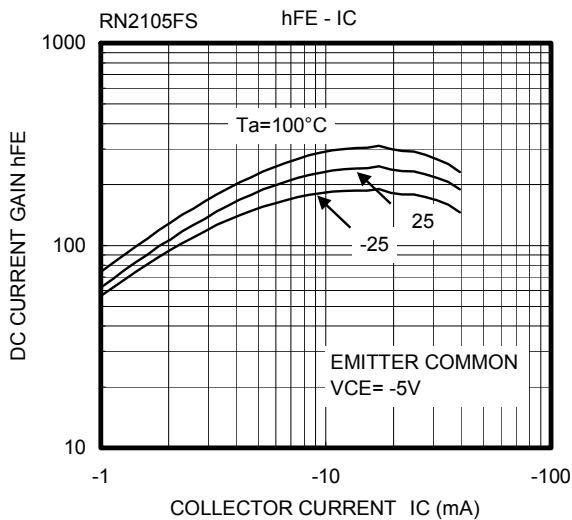
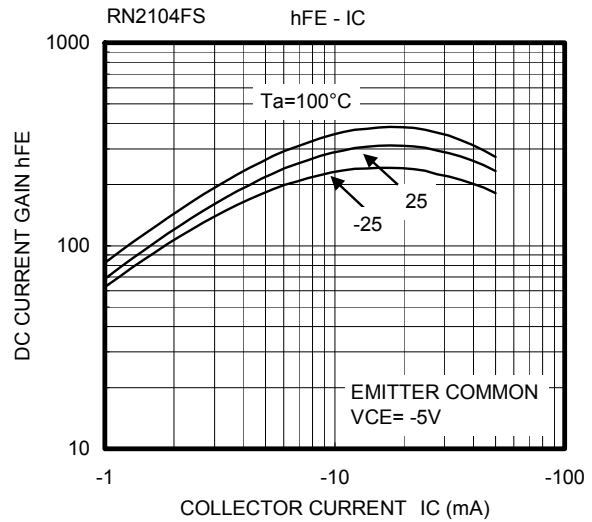
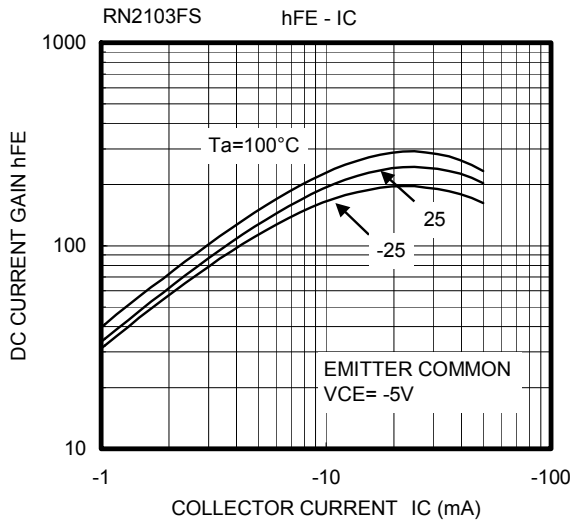
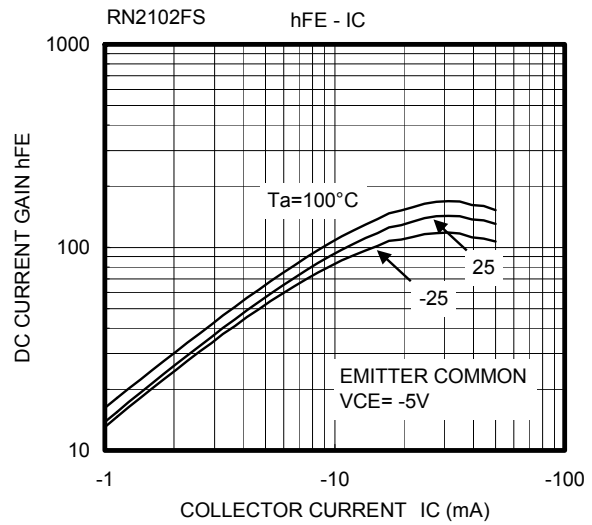
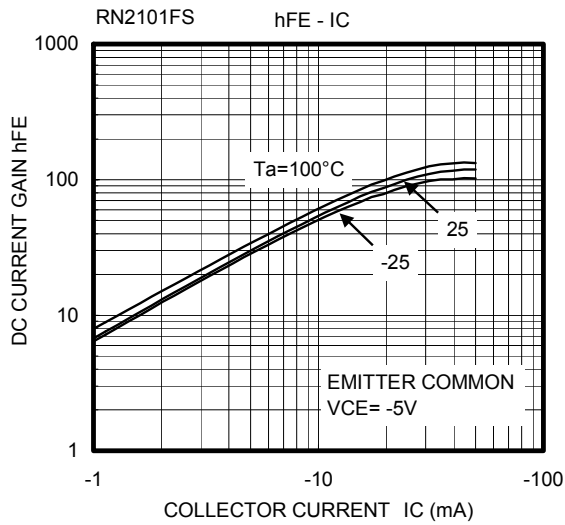
Characteristics		Symbol	Rating	Unit
Collector-base voltage	RN2101FS~2106FS	V <sub>CBO</sub>	-20	V
Collector-emitter voltage		V <sub>CEO</sub>	-20	V
Emitter-base voltage	RN2101FS~2104FS	V <sub>EBO</sub>	-10	V
	RN2105FS, 2106FS		-5	
Collector current	RN2101FS~2106FS	I <sub>C</sub>	-50	mA
Collector power dissipation		P <sub>C</sub>	50	mW
Junction temperature		T <sub>j</sub>	150	°C
Storage temperature range		T <sub>stg</sub>	-55~150	°C

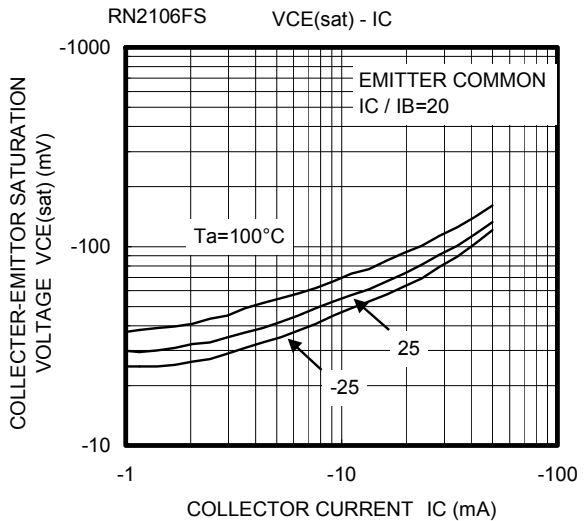
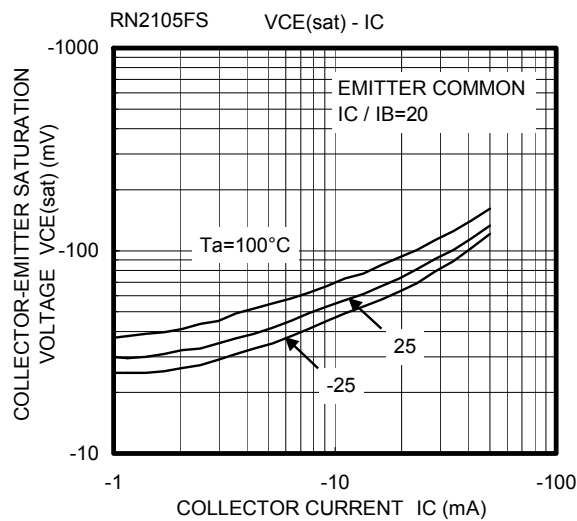
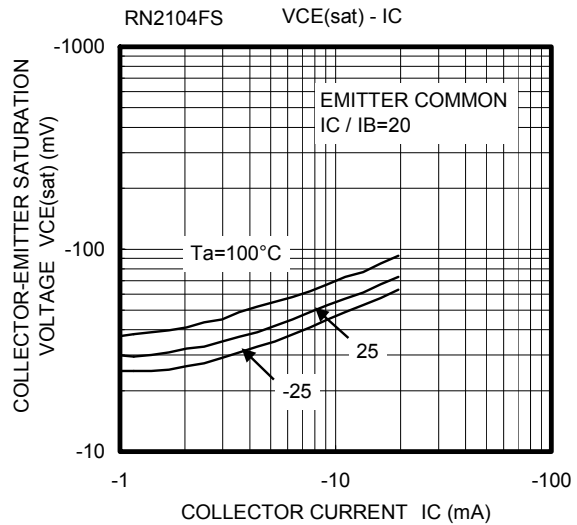
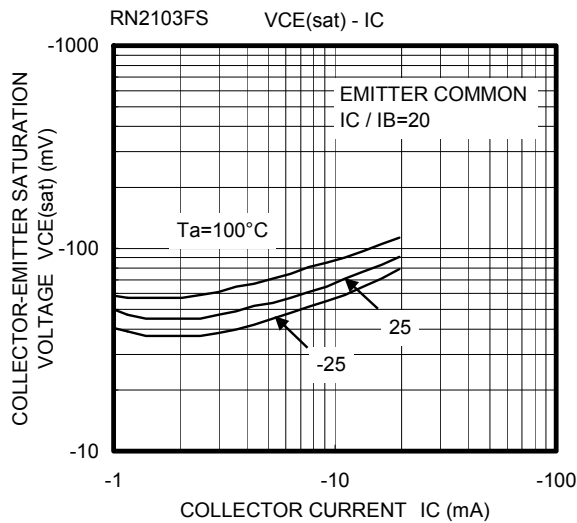
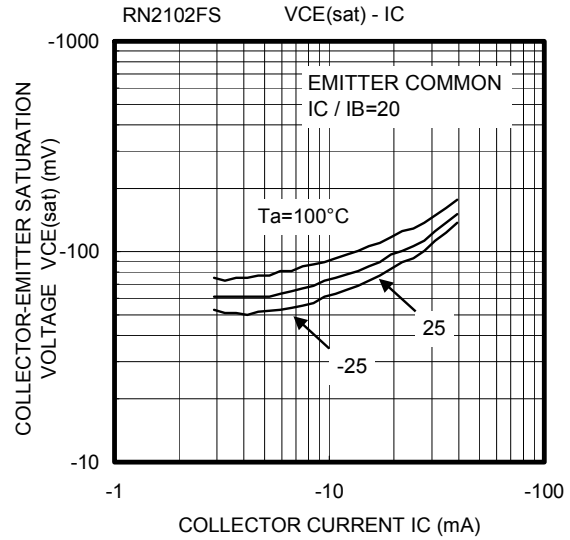
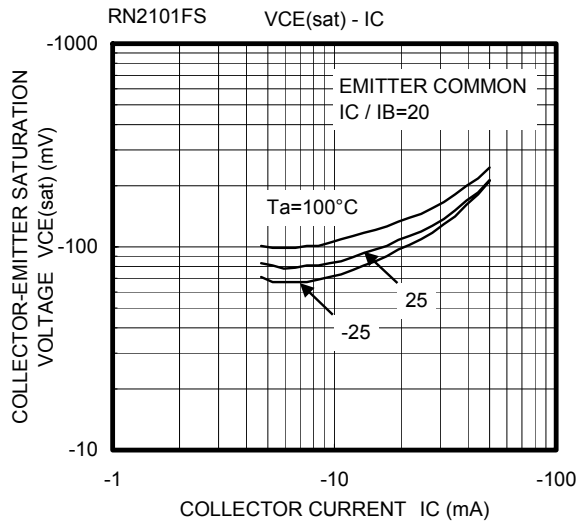
**Electrical Characteristics (Ta = 25°C)**

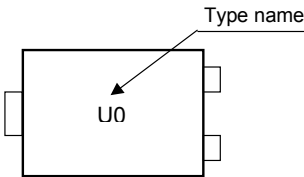
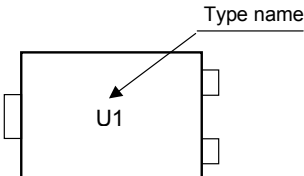
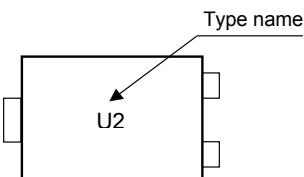
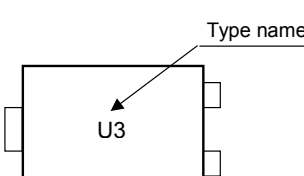
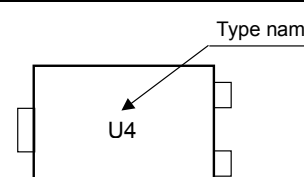
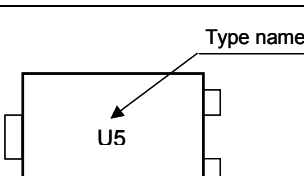
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	RN2101FS~2106FS	$I_{CBO}$	$V_{CB} = -20\text{ V}, I_E = 0$	—	—	-100	nA
		$I_{CEO}$	$V_{CE} = -20\text{ V}, I_B = 0$	—	—	-500	
Emitter cut-off current	RN2101FS	$I_{EBO}$	$V_{EB} = -10\text{ V}, I_C = 0$	-0.89	—	-1.33	mA
	RN2102FS			-0.41	—	-0.63	
	RN2103FS			-0.18	—	-0.29	
	RN2104FS			-0.088	—	-0.133	
	RN2105FS	$I_{EBO}$	$V_{EB} = -5\text{ V}, I_C = 0$	-0.085	—	-0.127	
	RN2106FS			-0.08	—	-0.121	
DC current gain	RN2101FS	$h_{FE}$	$V_{CE} = -5\text{ V}, I_C = -10\text{ mA}$	30	—	—	
	RN2102FS			60	—	—	
	RN2103FS			100	—	—	
	RN2104FS			120	—	—	
	RN2105FS			120	—	—	
	RN2106FS			120	—	—	
Collector-emitter saturation voltage	RN2101FS~2106FS	$V_{CE(sat)}$	$I_C = -5\text{ mA}, I_B = -0.25\text{ mA}$	—	—	-0.15	V
Input voltage (ON)	RN2101FS	$V_{I(ON)}$	$V_{CE} = -0.2\text{ V}, I_C = -5\text{ mA}$	-1.0	—	-2.0	V
	RN2102FS			-1.0	—	-2.2	
	RN2103FS			-1.1	—	-2.7	
	RN2104FS			-1.2	—	-3.6	
	RN2105FS			-0.6	—	-1.1	
	RN2106FS			-0.6	—	-1.2	
Input voltage (OFF)	RN2101FS~2104FS	$V_{I(OFF)}$	$V_{CE} = -5\text{ V}, I_C = -0.1\text{ mA}$	-0.8	—	-1.5	V
	RN2105FS, 2106FS			-0.4	—	-0.8	
Collector output capacitance	RN2101FS~2106FS	$C_{ob}$	$V_{CB} = -10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	1.2	—	pF
Input resistor	RN2101FS	R1	—	3.76	4.7	5.64	kΩ
	RN2102FS			8	10	12	
	RN2103FS			17.6	22	26.4	
	RN2104FS			37.6	47	56.4	
	RN2105FS			1.76	2.2	2.64	
	RN2106FS			3.76	4.7	5.64	
Resistor ratio	RN2101FS~2104FS	R1/R2	—	0.8	1.0	1.2	
	RN2105FS			0.0376	0.0468	0.0562	
	RN2106FS			0.08	0.1	0.12	









Type Name	Marking
RN2101FS	
RN2102FS	
RN2103FS	
RN2104FS	
RN2105FS	
RN2106FS	

## HANDLING PRECAUTION

When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

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